

INCHANGE SEMICONDUCTOR

G(1)

123

isc N-Channel MOSFET Transistor

2N0609

D(2)

S(3)

2, Drain

3. Source

pin 1, Gate

• FEATURES

Static drain-source on-resistance:

R⊳s(on)≤9.1mΩ

- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

- Ultra Low On-resistance
- Fast Switching

• ABSOI	LUTE MAXIMUM RATINGS(Ta=25°C	TO-220C package		
SYMBOL	PARAMETER	VALUE	UNIT	↓ = B → F → = S
V _{DSS}	Drain-Source Voltage	55	V	
V_{GS}	Gate-Source Voltage	±20	V	
ID	Drain Current-Continuous	100	A	
P _D	Total Dissipation @T _c =25℃	190	W	
Tj	Max. Operating Junction Temperature	175	°C	MIN MAX
T _{stg}	Storage Temperature	-55~175	°C	A 15.50 15.90 B 9.80 10.20 C 4.20 4.50 D 0.70 0.90
• THERN	IAL CHARACTERISTICS	F 3.40 3.70 G 4.98 5.18 H 2.68 2.90		
SYMBOL	PARAMETER	МАХ	UNIT	J 0.44 0.60 K 12.80 13.40 L 1.20 1.45
Rth(j-c)	Channel-to-case thermal resistance	0.79	°C/W	Q 2.70 2.90 R 2.30 2.70 S 1.29 1.35 U 6.45 6.65
				V 8.66 8.86

isc website: www.iscsemi.cn

1



isc N-Channel MOSFET Transistor

2N0609

ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	55			V
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =250	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =55A			9.1	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =55V; V _{GS} = 0V			25	μA
V _{SD}	Diode forward voltage	I _S =55A, V _{GS} = 0V			1.3	V

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.